

BREAKDOWN AND CAPACITANCE PROPERTIES OF SOME
TWO TERMINAL SILICON EPITAXIAL DEVICE STRUCTURES

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of the requirement for the degree of Doctor
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CERTIFICATE

This is to certify that the dissertation,
'Breakdown And Capacitance Properties of Some Two
Terminal Silicon Epitaxial Device Structures', which
is being submitted by Rajendra Kumar for the award
of the degree of Doctor of Philosophy to the Indian
Institute of Technology, New Delhi, is a record of
bonafide research work. He has carried out this
research work under my guidance and supervision.

This dissertation has reached the standard
fulfilling the requirements of the regulations
relating to the degree. The results obtained in
this dissertation have not been submitted to
any other University or Institute for the award of
any degree or diploma.

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